

AMENDMENTS TO THE SPECIFICATION

Paragraph [0024] of the electronically filed specification is amended to read as follows:

In Figure 6(d), the second resist layer 118 is removed and the exposed portions of the seed layer 110 are etched to complete the BLM formation. However, in this instance, the underetching of the seed layer 110 is with respect to the wider edges of the solder material 116, instead of the barrier layer 114. Accordingly, during a reflow process, the solder material 116 retracts in a self-defined manner to the copper layer of the seed layer 116 as a result of the wettability property of a copper surface relative to (molten) solder material. As shown in Figure 6(e), the reflow process thus insures a truncated, spherical-shaped solder ball with a structurally complete BLM TiW/CrCu/Cu stack corresponding to the dimensions of the barrier layer. Upon reflow, any thin copper atop the nickel/copper barrier layer, and part of the nickel is consumed in the intermetallic formation process. Figures 7(a) through 7(c) are SEM cross sections of a finished, reflowed C4 configured in accordance with the method illustrated in Figures 6(a) through 6(d).